

# Kin M Yu

## List of Publications by Year in descending order

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538  
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539  
all docs

539  
docs citations

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times ranked

12417  
citing authors

#	ARTICLE	IF	CITATIONS
1	Energy consumption modelling of a passive hybrid system for office buildings in different climates. Energy, 2022, 239, 121914.	4.5	14
2	Improved two-step photon absorption current by Cl-doping in ZnTeO-based intermediate band solar cells with n-ZnS layer. Solar Energy Materials and Solar Cells, 2022, 235, 111456.	3.0	4
3	Electronic structure and properties of Cu <sub>2-x</sub> S thin films: Dependence of phase structures and free-hole concentrations. Applied Surface Science, 2022, 572, 151530.	3.1	8
4	Amorphous CdO-In <sub>2</sub> O <sub>3</sub> alloy thin films with high conductivity and transparency synthesized by sol-gel method. Journal of Alloys and Compounds, 2022, 893, 162341.	2.8	5
5	Doping limitation due to self-compensation by native defects in In-doped rocksalt Cd <sub>x</sub> Zn <sub>1-x</sub> O. Journal of Physics Condensed Matter, 2022, 34, 065702.	0.7	1
6	On-wire axial perovskite heterostructures for monolithic dual-wavelength laser. Nano Energy, 2022, 92, 106778.	8.2	10
7	Effects of Al doping on the structural, electrical, and optical properties of rock-salt ZnCdO thin films grown by molecular beam epitaxy. Journal of Physics and Chemistry of Solids, 2022, 163, 110571.	1.9	3
8	Near-Infrared-Activated Thermochromic Perovskite Smart Windows. Advanced Science, 2022, 9, e2106090.	5.6	37
9	Effects of acceptor doping and oxygen stoichiometry on the properties of sputter-deposited p-type rocksalt Ni <sub>1-x</sub> Zn <sub>x</sub> O (0.3 <math>x</math>). Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 504	2.8	4
10	Improving the p-type conductivity of Cu <sub>2</sub> O thin films by Ni doping and their heterojunction with n-ZnO. Applied Surface Science, 2022, 590, 153047.	3.1	14
11	Controlling electrical and optical properties of wurtzite Cd <sub>x</sub> Zn <sub>1-x</sub> O with high Cd contents via native defects manipulation by low-temperature annealing. Journal of Applied Physics, 2022, 131, .	1.1	1
12	Optoelectronic properties and doping of magnetron sputtered highly mismatched ZnO <sub>1-x</sub> Te <sub>x</sub> alloy thin films. Journal of Alloys and Compounds, 2021, 852, 156950.	2.8	4
13	Effective decoupling of seebeck coefficient and the electrical conductivity through isovalent substitution of erbium in bismuth selenide thermoelectric material. Journal of Alloys and Compounds, 2021, 857, 157559.	2.8	18
14	Mechanism of non-catalytic chemical vapor deposition growth of all-inorganic CsPbX <sub>3</sub> (X) Tj ETQq0 0 0 rgBT /Overlock 10 T	2.7	6
15	Crystalline all-inorganic lead-free Cs <sub>3</sub> Sb <sub>2</sub> I <sub>9</sub> perovskite microplates with ultra-fast photoconductive response and robust thermal stability. Nano Research, 2021, 14, 4116-4124.	5.8	39
16	Organic Hybrid Perovskite (MAPb <sub>3</sub> Cl <sub>x</sub> ) for Thermochromic Smart Window with Strong Optical Regulation Ability, Low Transition Temperature, and Narrow Hysteresis Width. Advanced Functional Materials, 2021, 31, 2010426.	7.8	50
17	Self-Densified Optically Transparent VO <sub>2</sub> Thermochromic Wood Film for Smart Windows. ACS Applied Materials & Interfaces, 2021, 13, 22495-22504.	4.0	60
18	Highly transparent and conducting In doped CdO synthesized by sol-gel solution processing. Journal of Materials Science, 2021, 56, 12607-12619.	1.7	7

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19	Structural, optical, and electrical properties of WZ- and RS-ZnCdO thin films on MgO (100) substrate by molecular beam epitaxy. <i>Journal of Alloys and Compounds</i> , 2021, 867, 159033.	2.8	2
20	Thermochromic Smart Windows: Organic Hybrid Perovskite (MAPbI <sub>3</sub> Cl <sub>x</sub> ) for Thermochromic Smart Window with Strong Optical Regulation Ability, Low Transition Temperature, and Narrow Hysteresis Width ( <i>Adv. Funct. Mater.</i> 26/2021). <i>Advanced Functional Materials</i> , 2021, 31, 2170186.	7.8	4
21	Effect of Nitrogen Doping on Structural, Electrical, and Optical Properties of CuO Thin Films Synthesized by Radio Frequency Magnetron Sputtering for Photovoltaic Application. <i>ECS Journal of Solid State Science and Technology</i> , 2021, 10, 065019.	0.9	4
22	Two-Step Chemical Vapor Deposition-Synthesized Lead-Free All-Inorganic Cs <sub>3</sub> Sb <sub>2</sub> Br <sub>9</sub> Perovskite Microplates for Optoelectronic Applications. <i>ACS Applied Materials &amp; Interfaces</i> , 2021, 13, 35930-35940.	4.0	20
23	Flexibility of Room-Temperature-Synthesized Amorphous CdO-In <sub>2</sub> O <sub>3</sub> Alloy Films and Their Application as Transparent Conductors in Solar Cells. <i>ACS Applied Materials &amp; Interfaces</i> , 2021, 13, 43795-43805.	4.0	7
24	Effects of oxygen flow ratio and thermal annealing on defect evolution of aluminum doped zinc oxide thin films by reactive DC magnetron sputtering. <i>Journal of Physics Condensed Matter</i> , 2021, 33, 465703.	0.7	6
25	Electrical conductivity and effects of mechanical bending of flexible amorphous transparent conducting CdO-Ga <sub>2</sub> O <sub>3</sub> films synthesized by room temperature sputtering. <i>Journal of Alloys and Compounds</i> , 2021, 875, 160000.	2.8	6
26	Effects of free carriers on the optical properties of high mobility transition metal doped In <sub>2</sub> O <sub>3</sub> transparent conductors. <i>Physical Review Materials</i> , 2021, 5, .	0.9	7
27	Band alignment of wide bandgap NiO/MoO <sub>3</sub> and NiO/WO <sub>3</sub> p-n heterojunctions studied by high-resolution X-ray photoelectron spectroscopy. <i>Journal of Alloys and Compounds</i> , 2021, 876, 160136.	2.8	13
28	Potential building energy savings by passive strategies combining daytime radiative coolers and thermochromic smart windows. <i>Case Studies in Thermal Engineering</i> , 2021, 28, 101517.	2.8	21
29	Reversible photochromic and photoluminescence in iodide perovskites. <i>Thin Solid Films</i> , 2021, 737, 138950.	0.8	4
30	Nitrogen Doping Effect in Cu <sub>4</sub> O <sub>3</sub> Thin Films Fabricated by Radio Frequency Magnetron Sputtering. <i>Physica Status Solidi (B): Basic Research</i> , 2020, 257, 1900363.	0.7	5
31	Conduction band modifications by d states in vanadium doped CdO. <i>Journal of Alloys and Compounds</i> , 2020, 822, 153567.	2.8	6
32	Bio-inspired TiO <sub>2</sub> nano-cone antireflection layer for the optical performance improvement of VO <sub>2</sub> thermochromic smart windows. <i>Scientific Reports</i> , 2020, 10, 11376.	1.6	18
33	Controllable optical emission wavelength in all-inorganic halide perovskite alloy microplates grown by two-step chemical vapor deposition. <i>Nano Research</i> , 2020, 13, 2939-2949.	5.8	18
34	Morphology and strain control of hierarchical cobalt oxide nanowire electrocatalysts via solvent effect. <i>Nano Research</i> , 2020, 13, 3130-3136.	5.8	13
35	Vacancy defects induced changes in the electronic and optical properties of NiO studied by spectroscopic ellipsometry and first-principles calculations. <i>Journal of Applied Physics</i> , 2020, 128, .	1.1	42
36	Temperature-dependent growth of hexagonal and monoclinic gallium sulfide films by pulsed-laser deposition. <i>AIP Advances</i> , 2020, 10, 105215.	0.6	9

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37	Controlling the p-Type Conductivity and Composition Range for Bipolar Conduction in Ni <sub>x</sub> Cd <sub>1-x</sub> O Alloys by Acceptor Doping. Journal of Physical Chemistry C, 2020, 124, 20000-20009.	1.5	8
38	Synthesis of New Nitride Alloys with Mg by Plasma-Assisted Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 2020, 257, 2000122.	0.7	2
39	Realization of rocksalt Zn <sub>1-x</sub> Cd <sub>x</sub> O thin films with an optical band gap above 3.0 eV by molecular beam epitaxy. CrystEngComm, 2020, 22, 2781-2787.	1.3	8
40	Effect of oxygen flow rate on properties of Cu <sub>4</sub> O <sub>3</sub> thin films fabricated by radio frequency magnetron sputtering. Journal of Applied Physics, 2020, 127, .	1.1	12
41	Wide-Gap Zn <sub>1-x</sub> O Alloy: A Transparent p-Type Oxide. Physical Review Applied, 2020, 13, .	1.5	17
42	Room temperature sputtered Cu doped NiO <sub>1+δ</sub> : p-type conductivity, stability of electrical properties and p-n heterojunction. Journal of Alloys and Compounds, 2020, 835, 155269.	2.8	18
43	Rapid thermal annealing assisted facile solution method for tungsten-doped vanadium dioxide thin films on glass substrate. Journal of Alloys and Compounds, 2020, 833, 155053.	2.8	26
44	Efficient p-type doping of sputter-deposited NiO thin films with Li, Ag, and Cu acceptors. Physical Review Materials, 2020, 4, .	0.9	19
45	Electronically Controlled Chemical Stability of Compound Semiconductor Surfaces. ACS Applied Materials & Interfaces, 2019, 11, 32543-32551.	4.0	1
46	Cl-doping effect in ZnTe <sub>1-x</sub> O <sub>x</sub> highly mismatched alloys for intermediate band solar cells. Journal of Applied Physics, 2019, 125, 243109.	1.1	11
47	Sol-gel synthesis of highly transparent and conducting Cadmium Oxide. , 2019, , .		0
48	Stoichiometry Controlled Bipolar Conductivity in Nanocrystalline Ni <sub>x</sub> Cd <sub>1-x</sub> O. Physical Review Applied, 2019, 11, .	1.5	19
49	Effects of the host conduction band energy on the electronic band structure of ZnCdTeO dilute oxide alloys. Journal of Applied Physics, 2019, 126, 083106.	1.1	5
50	Composition tunable inorganic Lead Halide Perovskites microstructures synthesized by single and two-step chemical vapor deposition methods. , 2019, , .		0
51	Amorphous gallium oxide sulfide: A highly mismatched alloy. Journal of Applied Physics, 2019, 126, .	1.1	8
52	Three-dimensional band structure and surface electron accumulation of rs-CdxZn1-xO studied by angle-resolved photoemission spectroscopy. Scientific Reports, 2019, 9, 8026.	1.6	7
53	ZnO <sub>1-x</sub> Te <sub>x</sub> highly mismatched alloys beyond the dilute alloy limit: Synthesis and electronic band structure. Journal of Applied Physics, 2019, 125, 155702.	1.1	13
54	Oxygen Concentration Dependence of Photovoltaic Properties of Intermediate Band Solar Cells based on Cl-doped ZnTeO. , 2019, , .		0

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55	Mg induced compositional change in InGaN alloys. Semiconductor Science and Technology, 2019, 34, 025014.	1.0	3
56	Effects of doping and rapid thermal processing in Y doped CdO thin films. Journal of Alloys and Compounds, 2019, 776, 259-265.	2.8	12
57	Effects of oxygen stoichiometry on the phase stability of sputter-deposited $Cd_{1-x}Zn_xO$ thin films. Journal of Applied Physics, 2019, 125, 083101.	0.9	8
58	Room-Temperature-Synthesized High-Mobility Transparent Amorphous $Cd_{0.5}Ga_{0.5}O_{2.3}$ Alloys with Widely Tunable Electronic Bands. ACS Applied Materials & Interfaces, 2018, 10, 7239-7247.	4.0	24
59	Room-Temperature Red-Green-Blue Whispering-Gallery Mode Lasing and White-Light Emission from Cesium Lead Halide Perovskite ( $CsPbX_3$ , X = Cl, Br, I) Microstructures. Advanced Optical Materials, 2018, 6, 1700993.	3.6	47
60	Growth behavior of co-electrodeposited CZTS precursor thin films from acidic baths containing tartaric acid. Materials Chemistry and Physics, 2018, 204, 83-94.	2.0	19
61	Oxygen vibrational modes in $Zn_{1-x}O_x$ alloys. Journal of Applied Physics, 2018, 123, .	1.1	4
62	Engineering Electronic Band Structure of Indium-doped $Cd_{1-x}Mg_xO$ Alloys for Solar Power Conversion Applications. Energy Technology, 2018, 6, 122-126.	1.8	5
63	THz transient photoconductivity of the III-V dilute nitride $GaP_{1-y}As_yN_x$ . Semiconductor Science and Technology, 2018, 33, 125009.	1.0	3
64	Improved photovoltaic properties of ZnTeO-based intermediate band solar cells. , 2018, , .		2
65	Multiband modification of III-V dilute nitrides for IBSC application. , 2017, , .		1
66	Growth and characterization of Zn <sub>1-x</sub> Cd <sub>x</sub> Te <sub>1-y</sub> O <sub>y</sub> highly mismatched alloys for intermediate band solar cells. Solar Energy Materials and Solar Cells, 2017, 169, 1-7.	3.0	9
67	Improved Open-Circuit Voltage and Photovoltaic Properties of ZnTeO-Based Intermediate Band Solar Cells With n-Type ZnS Layers. IEEE Journal of Photovoltaics, 2017, 7, 1024-1030.	1.5	12
68	Multicolor emission from intermediate band semiconductor $ZnO_{1-x}S_x$ . Scientific Reports, 2017, 7, 44214.	1.6	19
69	High mobility transparent amorphous CdO-In <sub>2</sub> O <sub>3</sub> alloy films synthesized at room temperature. Applied Physics Letters, 2017, 111, .	1.5	12
70	Effects of Ni-d-levels on the electronic band structure of $Ni_xCd_{1-x}O$ semiconducting alloys. Journal of Applied Physics, 2017, 122, .	1.1	9
71	Surface modification of NiCdO barrier layer in complex photoanodes and TiO <sub>2</sub> protective coating for efficient and stable water dissociation. Journal of Solid State Electrochemistry, 2017, 21, 803-812.	1.2	0
72	On the Use of Transparent Conductive Oxides in High Concentrator III-V Multijunction Solar Cells. , 2017, , .		1

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73	Intermixing studies in GaN <sub>1-x</sub> Sb <sub>x</sub> highly mismatched alloys. Applied Optics, 2017, 56, B64.	2.1	3
74	Effect of Cl-doping in ZnTeO on Photoluminescence and Photovoltaic Properties of ZnTeO-based Intermediate Band Solar Cells. , 2017, , .		0
75	Undoped p-type GaN <sub>1-x</sub> Sb <sub>x</sub> alloys: Effects of annealing. Applied Physics Letters, 2016, 109, .	1.5	6
76	Band structure of germanium carbides for direct bandgap silicon photonics. Journal of Applied Physics, 2016, 120, .	1.1	25
77	Designing III-V dilute nitride alloys for IBSC application. , 2016, , .		0
78	Defects and properties of cadmium oxide based transparent conductors. Journal of Applied Physics, 2016, 119, .	1.1	32
79	Effects of Free Carriers on the Optical Properties of Doped CdO for Full-Spectrum Photovoltaics. Physical Review Applied, 2016, 6, .	1.5	54
80	Cl-doping in highly mismatched ZnTe <sub>1-x</sub> O <sub>x</sub> alloys for intermediate band solar cells. , 2016, , .		0
81	Semiempirical modeling of a three sublayer photoanode for highly efficient photoelectrochemical water splitting: Parameter and electrolyte optimizations. Solar Energy Materials and Solar Cells, 2016, 157, 190-199.	3.0	3
82	Improvement in the electronic quality of pulsed laser deposited CuIn <sub>0.7</sub> Ga <sub>0.3</sub> Se <sub>2</sub> thin films via post-deposition elemental sulfur annealing process. Thin Solid Films, 2016, 608, 50-56.	0.8	11
83	Band structure of germanium carbides for direct bandgap photonics. , 2016, , .		0
84	Formation of Nanoscale Composites of Compound Semiconductors Driven by Charge Transfer. Nano Letters, 2016, 16, 5247-5254.	4.5	9
85	On-Nanowire Axial Heterojunction Design for High-Performance Photodetectors. ACS Nano, 2016, 10, 8474-8481.	7.3	88
86	Mechanistic insights into chemical and photochemical transformations of bismuth vanadate photoanodes. Nature Communications, 2016, 7, 12012.	5.8	231
87	Highly mismatched GaN <sub>1-x</sub> Sb <sub>x</sub> alloys: synthesis, structure and electronic properties. Semiconductor Science and Technology, 2016, 31, 083001.	1.0	16
88	Multicolor Electroluminescence from Intermediate Band Solar Cell Structures. Advanced Energy Materials, 2016, 6, 1501820.	10.2	13
89	Compositional dependence of optical transition energies in highly mismatched Zn <sub>1-x</sub> Cd <sub>x</sub> Te <sub>1-y</sub> O <sub>y</sub> alloys. Applied Physics Express, 2016, 9, 021202.	1.1	7
90	Electrochemical modification of the optical and electrical properties of Cd-rich Ni Cd <sub>1-x</sub> O alloys. Solar Energy Materials and Solar Cells, 2016, 147, 127-133.	3.0	6

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91	Controlling disorder-mediated exchange bias in (Mn,Zn,Fe)3O4 thin films. Journal of Magnetism and Magnetic Materials, 2016, 405, 129-136.	1.0	5
92	Semiempirical Modelling of a Nanostructured Photoanode Profile for Highly Efficient Water Splitting: Three Sublayers Concept. Journal of Green Engineering (discontinued), 2016, 5, 97-112.	0.7	0
93	Growth and characterization of highly mismatched Zn <sub>1-x</sub> Cd <sub>x</sub> Te <sub>1-y</sub> O <sub>y</sub> alloys for intermediate band solar cells. , 2015, , .		1
94	Evidence of extreme type-III band offset at buried CdO/SnTe interfaces. Physical Review B, 2015, 91, .	11.7	7
95	Growth and characterization of ZnO <sub>1-x</sub> S <sub>x</sub> highly mismatched alloys over the entire composition. Journal of Applied Physics, 2015, 118, .	1.1	43
96	Electronic band structure of highly mismatched GaN <sub>1-x</sub> Sb <sub>x</sub> alloys in a broad composition range. Applied Physics Letters, 2015, 107, .	1.5	25
97	Fabrication and characterization of multiband solar cells based on highly mismatched alloys. Journal of Physics: Conference Series, 2015, 647, 012067.	0.3	0
98	Self-Passivation of Defects: Effects of High-Energy Particle Irradiation on the Elastic Modulus of Multilayer Graphene. Advanced Materials, 2015, 27, 6841-6847.	11.1	24
99	Simultaneous Enhancement of Electrical Conductivity and Thermopower of Bi <sub>2</sub> Te <sub>3</sub> by Multifunctionality of Native Defects. Advanced Materials, 2015, 27, 3681-3686.	11.1	97
100	Electronic band structure of ZnO-rich highly mismatched ZnO <sub>1-x</sub> Te <sub>x</sub> alloys. Applied Physics Letters, 2015, 106, .	1.5	27
101	Determination of N/Ga-rich growth conditions, using in-situ auger electron spectroscopy. Journal of Crystal Growth, 2015, 425, 2-4.	0.7	3
102	Bi flux-dependent MBE growth of GaSbBi alloys. Journal of Crystal Growth, 2015, 425, 241-244.	0.7	27
103	Ni <sub>x</sub> Cd <sub>1-x</sub> O: Semiconducting alloys with extreme type III band offsets. Applied Physics Letters, 2015, 106, .	1.5	20
104	Effects of a semiconductor matrix on the band anticrossing in dilute group II-VI oxides. Semiconductor Science and Technology, 2015, 30, 085018.	1.0	18
105	InGaN pn-junctions grown by PA-MBE: Material characterization and fabrication of nanocolumn electroluminescent devices. Journal of Crystal Growth, 2015, 425, 393-397.	0.7	8
106	Electron Barrier Engineering in a Thin-Film Intermediate-Band Solar Cell. IEEE Journal of Photovoltaics, 2015, 5, 878-884.	1.5	10
107	Effects of native defects on properties of low temperature grown, non-stoichiometric gallium nitride. Journal Physics D: Applied Physics, 2015, 48, 385101.	1.3	6
108	Exploration of the growth parameter space for MBE-grown GaN <sub>1-x</sub> Sb <sub>x</sub> highly mismatched alloys. Journal of Crystal Growth, 2015, 425, 255-257.	0.7	8



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109	Temperature evolution of carrier dynamics in GaN <sub>x</sub> PyAs <sub>1-y</sub> alloys. Journal of Applied Physics, 2015, 117, .	1.1	18
110	Effects of the d-donor level of vanadium on the properties of Zn <sub>1-x</sub> V <sub>x</sub> O films. Applied Physics Letters, 2015, 106, .	1.5	12
111	Indium doped Cd <sub>1-x</sub> Zn <sub>x</sub> O alloys as wide window transparent conductors. Thin Solid Films, 2015, 597, 183-187.	0.8	7
112	Highly Uniform and Stable n-Type Carbon Nanotube Transistors by Using Positively Charged Silicon Nitride Thin Films. Nano Letters, 2015, 15, 392-397.	4.5	92
113	Bi-induced band gap reduction in epitaxial InSbBi alloys. Applied Physics Letters, 2014, 105, .	1.5	48
114	Improved ion implant fluence uniformity in hydrogen enhanced glow discharge plasma immersion ion implantation into silicon. Review of Scientific Instruments, 2014, 85, 063506.	0.6	2
115	Facile Synthesis of [Cu(SCH <sub>3</sub> ) <sub>3</sub> ] <sub>z</sub> Nanowires with High Charge Mobility. ChemPlusChem, 2014, 79, 559-563.	1.3	11
116	Composition determination of quaternary GaAsPN layers from single X-ray diffraction measurement of quasi-forbidden (002) reflection. Journal of Applied Physics, 2014, 115, .	1.1	8
117	Fermi level stabilization and band edge energies in CdxZn <sub>1-x</sub> O alloys. Journal of Applied Physics, 2014, 115, .	1.1	37
118	Surface photovoltage and modulation spectroscopy of E <sub>a</sub> <sup>-</sup> and E <sub>+</sub> transitions in GaNAs layers. Thin Solid Films, 2014, 567, 101-104.	0.8	17
119	Charge transfer and mobility enhancement at CdO/SnTe heterointerfaces. Applied Physics Letters, 2014, 105, 132103.	1.5	26
120	Composition and optical properties of dilute-Sb GaN <sub>1-x</sub> Sb <sub>x</sub> highly mismatched alloys grown by MBE. Journal Physics D: Applied Physics, 2014, 47, 465102.	1.3	9
121	Fermi-level stabilization in the topological insulators Bi <sub>2</sub> Se <sub>3</sub> . Physical Review B, 2014, 89, 041407.	1.1	11
122	Modeling of the atomic structure and electronic properties of amorphous GaN <sub>1-x</sub> As <sub>x</sub> . Computational Materials Science, 2014, 82, 100-106.	1.4	15
123	Growth and characterization of highly mismatched GaN <sub>1-x</sub> Sb <sub>x</sub> alloys. Journal of Applied Physics, 2014, 116, .	1.1	20
124	InGaN doping for high carrier concentration in plasma-assisted molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 381-384.	0.8	13
125	Surface hole accumulation and Fermi level stabilization energy in SnTe. Applied Physics Express, 2014, 7, 091201.	1.1	7
126	Theoretical and experimental studies of electronic band structure for GaSb <sub>1-x</sub> Bi <sub>x</sub> in the dilute Bi regime. Journal Physics D: Applied Physics, 2014, 47, 355107.	1.3	50



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127	High Bi content GaSbBi alloys. Journal of Applied Physics, 2014, 116, .	1.1	70
128	Tellurium n-type doping of highly mismatched amorphous GaN $\hat{1}$ As alloys in plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2014, 404, 9-13.	0.7	3
129	Substitutionality of nitrogen atoms and formation of nitrogen complexes and point defects in GaPN alloys. Journal Physics D: Applied Physics, 2014, 47, 075106.	1.3	12
130	Photogenerated Current By Two-Step Photon Excitation in ZnTeO Intermediate Band Solar Cells with n-ZnO Window Layer. IEEE Journal of Photovoltaics, 2014, 4, 196-201.	1.5	25
131	Effect of Sb on GaNAs Intermediate Band Solar Cells. IEEE Journal of Photovoltaics, 2013, 3, 730-736.	1.5	29
132	Growth and properties of GaSbBi alloys. Applied Physics Letters, 2013, 103, 142106.	1.5	84
133	Single crystalline In $\hat{1}$ Ga $\hat{1}$ xN layers on germanium by molecular beam epitaxy. CrystEngComm, 2013, 15, 9121.	1.3	6
134	Temperature dependence of the band gap of GaSb $\hat{1}$ xBi alloys with $0 \leq x \leq 0.042$ determined by photoreflectance. Applied Physics Letters, 2013, 103, .	1.5	46
135	Material properties of Cd<math>\hat{1}</math>Mg<math>\hat{1}</math>O transparent conductors. , 2013, , .		0
136	Molecular beam epitaxial growth of ZnCdTeO epilayers for intermediate band solar cells. Journal of Crystal Growth, 2013, 378, 259-262.	0.7	15
137	Microstructure of GaN $\hat{1}$ x Bi x. Journal of Electronic Materials, 2013, 42, 26-32.	1.0	5
138	GaNAsP: An intermediate band semiconductor grown by gas-source molecular beam epitaxy. Applied Physics Letters, 2013, 102, .	1.5	37
139	Photocurrent induced by two-photon excitation in ZnTeO intermediate band solar cells. Applied Physics Letters, 2013, 102, .	1.5	61
140	Crystal structure and properties of Cd $\hat{1}$ Zn $\hat{1}$ xO alloys across the full composition range. Applied Physics Letters, 2013, 102, .	1.5	60
141	GaN $\hat{1}$ xSbx highly mismatched alloys grown by low temperature molecular beam epitaxy under Ga-rich conditions. Journal of Crystal Growth, 2013, 383, 95-99.	0.7	14
142	Molecular beam epitaxy of highly mismatched N-rich GaN $\hat{1}$ xSbx and InN $\hat{1}$ xAsx alloys. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, .	0.6	12
143	In-rich InGaN thin films: Progress on growth, compositional uniformity, and doping for device applications. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, .	0.6	12
144	Microstructure of Mg doped GaNAs alloys. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 453-456.	0.8	1

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145	Highly mismatched N-rich GaN $_{1-x}$ Sbx films grown by low temperature molecular beam epitaxy. Applied Physics Letters, 2013, 102, .	1.5	26
146	P-type and undoped InGaN across the entire alloy composition range. , 2013, , .		0
147	Local structure of amorphous GaN $_{1-x}$ Asx semiconductor alloys across the composition range. Journal of Applied Physics, 2013, 113, .	1.1	6
148	P-type InGaN across the entire alloy composition range. Applied Physics Letters, 2013, 102, 102111.	1.5	13
149	Material properties of Cd $_{1-x}$ MgxO alloys synthesized by radio frequency sputtering. Applied Physics Letters, 2013, 103, .	1.5	21
150	Effect of Sb on GaNAs intermediate band solar cells. , 2013, , .		0
151	Electrical activation and electron spin resonance measurements of implanted bismuth in isotopically enriched silicon-28. Applied Physics Letters, 2012, 100, .	1.5	47
152	Red-green luminescence in indium gallium nitride alloys investigated by high pressure optical spectroscopy. Applied Physics Letters, 2012, 100, 162103.	1.5	14
153	Structural and optical studies of nitrogen incorporation into GaSb-based GaInSb quantum wells. Applied Physics Letters, 2012, 100, 021103.	1.5	13
154	On the electrical conductivity of Ti-implanted alumina. Journal of Applied Physics, 2012, 111, 063714.	1.1	9
155	Tuning structural, electrical, and optical properties of oxide alloys: ZnO $_{1-x}$ Sex. Journal of Applied Physics, 2012, 111, .	1.1	14
156	Transparent conductors for full spectrum photovoltaics. , 2012, , .		0
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